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APPLICATION NO.	FILING DATÉ	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/023,861	12/21/2001	Jae Soon Kwon	10729-P6746US0	5715
7590 10/15/2003			EXAMINER	
JACOBSON		TRAN, BINH X		
PROFESSIONAL LIMITED LIABILITY COMPANY 400 SEVENTH STREET, N.W. WASHINGTON, DC 20004			ART UNIT	PAPER NUMBER
			1765	

DATE MAILED: 10/15/2003

Please find below and/or attached an Office communication concerning this application or proceeding.

	Application No.	Applicant(s)
	10/023,861	KWON, JAE SOON
Office Action Summary	Examiner	Art Unit
	Binh X Tran	1765
The MAILING DATE of this communication Period for Reply	appears on the cover she	et with the correspondence address
A SHORTENED STATUTORY PERIOD FOR RE THE MAILING DATE OF THIS COMMUNICATIO - Extensions of time may be available under the provisions of 37 CFI after SIX (6) MONTHS from the mailing date of this communication - If the period for reply specified above is less than thirty (30) days, a - If NO period for reply is specified above, the maximum statutory pe - Failure to reply within the set or extended period for reply will, by st - Any reply received by the Office later than three months after the m earned patent term adjustment. See 37 CFR 1.704(b). Status	N. R 1.136(a). In no event, however, m. reply within the statutory minimum riod will apply and will expire SIX (6) atute, cause the application to become	ay a reply be timely filed of thirty (30) days will be considered timely. MONTHS from the mailing date of this communication. ne ABANDONED (35 U.S.C. § 133).
1) Responsive to communication(s) filed on	<u> 21 December 2001</u> .	·
2a) ☐ This action is FINAL . 2b) ⊠	This action is non-final.	
3) Since this application is in condition for all closed in accordance with the practice under the condition of the condit		
Disposition of Claims	•	
4)⊠ Claim(s) <u>1-7</u> is/are pending in the applicati		
4a) Of the above claim(s) is/are with	drawn from consideration	
5) Claim(s) is/are allowed.	•	
6)⊠ Claim(s) <u>1,2,4,6 and 7</u> is/are rejected.		
7)⊠ Claim(s) <u>3 and 5</u> is/are objected to.		
8) Claim(s) are subject to restriction ar	d/or election requirement	
Application Papers		
9) The specification is objected to by the Exam		
10) The drawing(s) filed on is/are: a) a		
Applicant may not request that any objection t		
11) Tile proposed drawing correction filed on		disapproved by the Examiner.
If approved, corrected drawings are required in 12) The oath or declaration is objected to by the		
•	Examiner.	
Priority under 35 U.S.C. §§ 119 and 120		0.0440(-) (-) (0.
13) △ Acknowledgment is made of a claim for for	eign prionty under 35 U.S	.C. § 119(a)-(d) or (f).
a)⊠ All b) Some * c) None of:		•
1. Certified copies of the priority docum		
2. Certified copies of the priority docum		
3. Copies of the certified copies of the paper application from the International * See the attached detailed Office action for a	Bureau (PCT Rule 17.2(a)).
14) Acknowledgment is made of a claim for dom	·	
a) The translation of the foreign language	provisional application ha	as been received.
15) Acknowledgment is made of a claim for dom Attachment(s)	resule priority under 35 U.	38 120 dila/01 121.
1) Notice of References Cited (PTO-892)	4) Inter	riew Summary (PTO-413) Paper No(s)
 Notice of References Cited (PTO-692) Notice of Draftsperson's Patent Drawing Review (PTO-948) Information Disclosure Statement(s) (PTO-1449) Paper Not 	5) Notic	e of Informal Patent Application (PTO-152)
J.S. Patent and Trademark Office PTOL-326 (Rev. 04-01) Offic	e Action Summary	Part of Paper No. 4

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DETAILED ACTION

Claim Objections

1. Claim 5 is objected to because of the following informalities: In lines 17 and 21of claim 5, the examiner suggests replacing "epi-layer" with --epitaxial layer-- in order to avoid any confusion whether or not "epi" stands for "epitaxial". Appropriate correction is required.

Double Patenting

2. Applicant is advised that should claim 2, 4 be found allowable, claims 6-7 will be objected to under 37 CFR 1.75 as being a substantial duplicate thereof. When two claims in an application are duplicates or else are so close in content that they both cover the same thing, despite a slight difference in wording, it is proper after allowing one claim to object to the other as being a substantial duplicate of the allowed claim.

See MPEP § 706.03(k).

Claim Rejections - 35 USC § 102

3. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

(e) the invention was described in a patent granted on an application for patent by another filed in the United States before the invention thereof by the applicant for patent, or on an international application by another who has fulfilled the requirements of paragraphs (1), (2), and (4) of section 371(c) of this title before the invention thereof by the applicant for patent.

The changes made to 35 U.S.C. 102(e) by the American Inventors Protection Act of 1999 (AIPA) and the Intellectual Property and High Technology Technical

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Amendments Act of 2002 do not apply when the reference is a U.S. patent resulting directly or indirectly from an international application filed before November 29, 2000. Therefore, the prior art date of the reference is determined under 35 U.S.C. 102(e) prior to the amendment by the AIPA (pre-AIPA 35 U.S.C. 102(e)).

4. Claims 1-2, 4, 6-7 are rejected under 35 U.S.C. 102(e) as being anticipated by Thei et al. (US 6,350,662).

Thei discloses a method comprising the steps of:

providing a semiconductor substrate (50) where a device isolation region was defined;

forming a mask on the substrate in such manner that the device isolation is exposed through the mask (Fig 3);

etching the substrate using the mask to form a trench (Fig 4, col. 3 lines 46-55); thermally treating an inner wall of the trench using the mask under hydrogen atmosphere (col. 3 lines 55 to col. 4 line 6);

forming a first insulating layer (66) covering the resulting inner wall of the trench (Fig 5);

forming a second insulating layer (74) on the mask in such a manner that the second insulating film (74) covers the first insulating film (66) (See Fig 7);

firstly etching the second insulating layer (74) to expose a surface of the mask (Fig 8, col. 4 lines 28-35);

removing the mask (58) (See Fig 9, col. 4 lines 35-37);

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secondly etching the remaining second insulating layer (74) until a surface of the substrate (50) is exposed, thereby forming a device isolation film (Fig 9-10; col. 4 lines 37-43).

Respect to claims 2 and 6, Thei teaches the thermal treatment is carried out at a temperature of 800 °C to 900 °C (col. 4 lines 1-5, within applicant's range of 600-1300 °C). Respect to claims 4 and 7, Thei teaches the first and second etch step are carried out using a chemical mechanical polishing or etch back process.

Allowable Subject Matter

- 5. Claim 3 would objected to as being dependent upon a rejected base claim, but would be allowable if rewritten in independent form including all of the limitations of the base claim and any intervening claims.
- 6. Claim 5 is objected to because of the minor informality as discussed above, but would be allowable if rewritten to correct the minor informality.
- The following is a statement of reasons for the indication of allowable subject matter: The cited prior arts fail to disclose or suggest the either one of the following step in conjunction with other limitation in the claim: forming an insulating layer covering the resulting of the inner wall of the trench using epitaxial grown process, or forming an epitaxial layer covering the resulting inner wall of the trench.

Conclusion

8. The prior art made of record and not relied upon is considered pertinent to applicant's disclosure.

Chen et al. (US 6,306,723) and Yew et al. (US 5,906,299).

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9. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Binh X Tran whose telephone number is (703) 308-1867. The examiner can normally be reached on Monday-Thursday and every other Friday.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Nadine G Norton can be reached on (703) 305-2667. The fax phone number for the organization where this application or proceeding is assigned is (703) 872-9306.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is (703) 308-0661.

Binh X. Tran

NADINE G. NORTON PRIMARY EXAMINER